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FAIRCHILD SEMICONDUCTOR®

December 2013

FCPF7N60NT

N-Channel MOSFET

600 V, 6.8 A, 0.52 Ω

Features

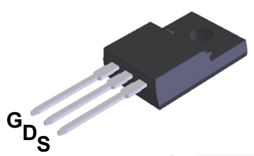
- Typ $R_{DS(on)}$ = 460mΩ
- Ultra Low Gate Charge (typ. Q_g = 17.8 nC)
- Low Effective Output Capacitance (typ. $C_{oss(eff.)}$ = 91 pF)
- 100% Avalanche Tested
- RoHS Compliant

Application

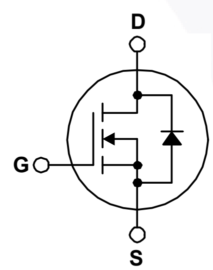
- Solar Inverter
- AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.



TO-220F



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FCPF7N60NT	Units
V_{DSS}	Drain to Source Voltage		600	V
V_{GSS}	Gate to Source Voltage		±30	V
I_D	Drain Current	-Continuous (T_C = 25°C)	6.8*	A
		-Continuous (T_C = 100°C)	4.3*	
I_{DM}	Drain Current	- Pulsed (Note 1)	20.4	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		79.4	mJ
I_{AR}	Avalanche Current		6.8	A
E_{AR}	Repetitive Avalanche Energy		0.6	mJ
dv/dt	MOSFET dv/dt Ruggedness		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		4.9	V/ns
P_D	Power Dissipation	(T_C = 25°C)	30.5	W
		- Derate above 25°C	0.24	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCPF7N60NT	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	4.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCPF7N60NT	FCPF7N60NT	TO-220F	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 1mA, V_{GS} = 0V, T_C = 25°C	600	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 1mA, Referenced to 25°C	-	0.6	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 480V, V_{GS} = 0V	-	-	10	μA
		V_{DS} = 480V, V_{GS} = 0V, T_C = 125°C	-	-	100	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, I_D = 250μA	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 3.4A	-	0.46	0.52	Ω
g_{FS}	Forward Transconductance	V_{DS} = 20V, I_D = 3.4A	-	8.5	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 100V, V_{GS} = 0V f = 1MHz	-	719	960	pF
C_{oss}	Output Capacitance		-	30	40	pF
C_{rss}	Reverse Transfer Capacitance		-	2.1	3.2	pF
C_{oss}	Output Capacitance	V_{DS} = 380V, V_{GS} = 0V, f = 1MHz	-	17	-	pF
$C_{oss}eff$	Effective Output Capacitance	V_{DS} = 0V to 380V, V_{GS} = 0V	-	91	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 380V, I_D = 3.4A V_{GS} = 10V (Note 4)	-	17.8	35.6	nC
Q_{gs}	Gate to Source Gate Charge		-	3.2	6.3	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	6.0	11.9	nC
ESR	Equivalent Series Resistance (G-S)	Drain Open	-	2.5	-	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 380V, I_D = 3.4A R_G = 4.7Ω (Note 4)	-	12	24	ns
t_r	Turn-On Rise Time		-	6	22	ns
$t_{d(off)}$	Turn-Off Delay Time		-	35	80	ns
t_f	Turn-Off Fall Time		-	12	24	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	6.8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20.4	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} =3.4A	-	-	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 3.4A dI_F/dt = 100A/μs	-	211	-	ns
Q_{rr}	Reverse Recovery Charge		-	1.8	-	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 12A, V_{DD} = 50V, R_G = 25Ω, starting T_J = 25°C.
3. I_{SD} ≤ 36A, di/dt ≤ 200A/μs, V_{DD} = 380V starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

Figure 1. On-Region Characteristics

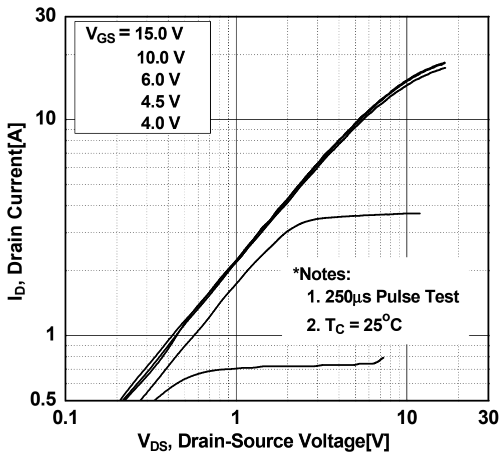


Figure 2. Transfer Characteristics

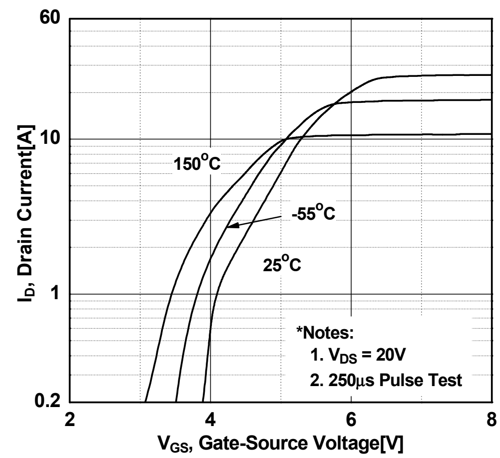


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

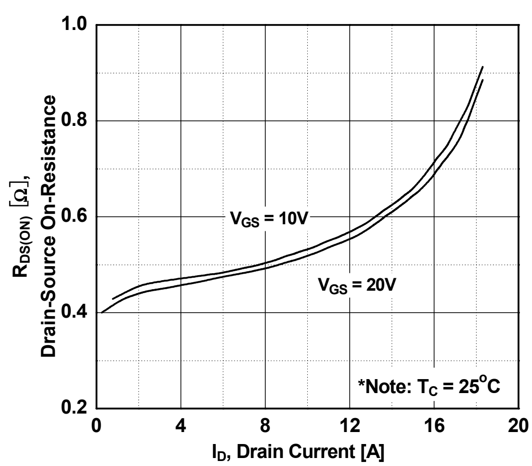


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

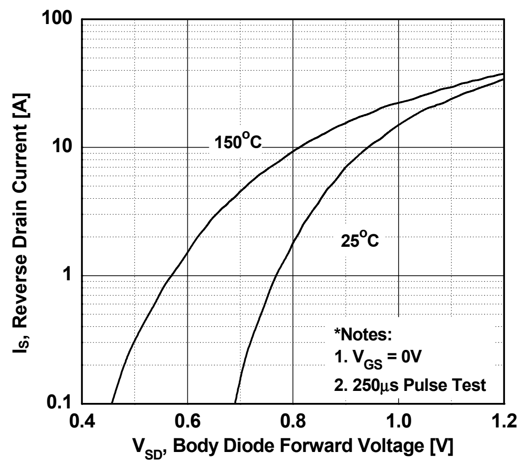


Figure 5. Capacitance Characteristics

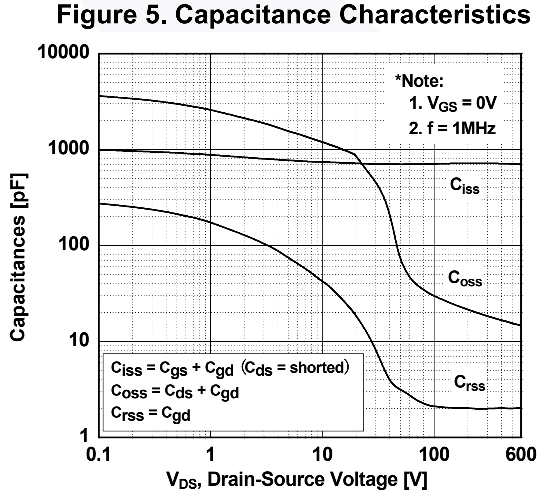
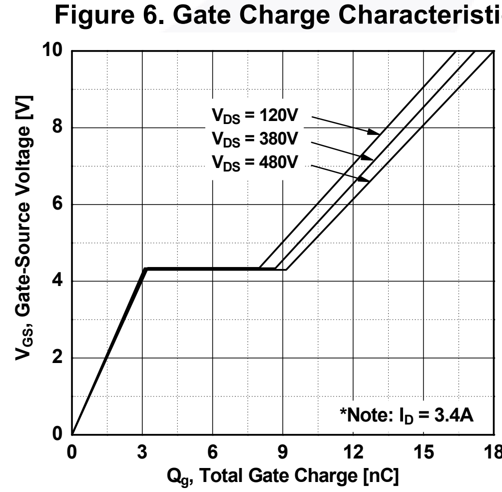


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

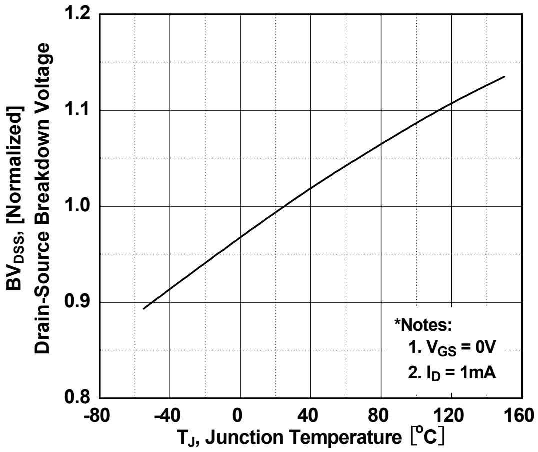


Figure 8. On-Resistance Variation vs. Temperature

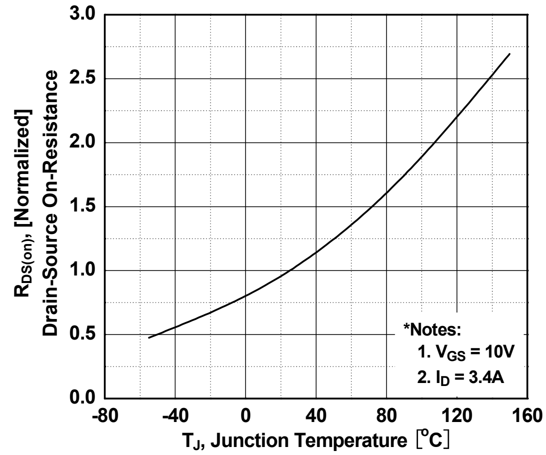


Figure 9. Maximum Safe Operating Area _ FCPF7N60NT

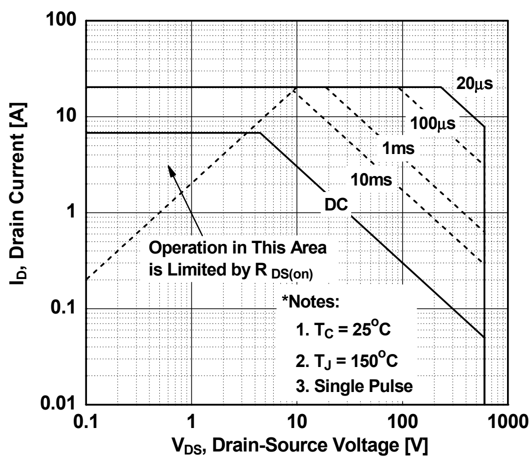
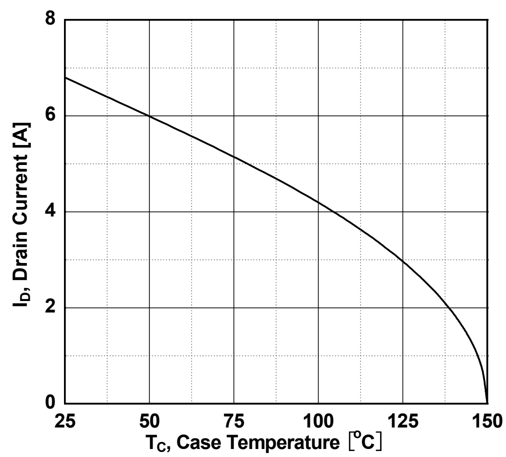


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Characteristics (Continued)

Figure 11. Transient Thermal Response Curve _ FCPF7N60NT

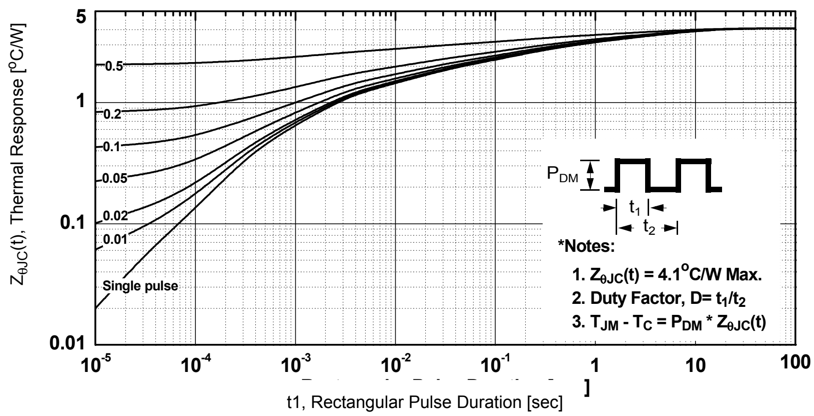


Figure 12. Gate Charge Test Circuit & Waveform

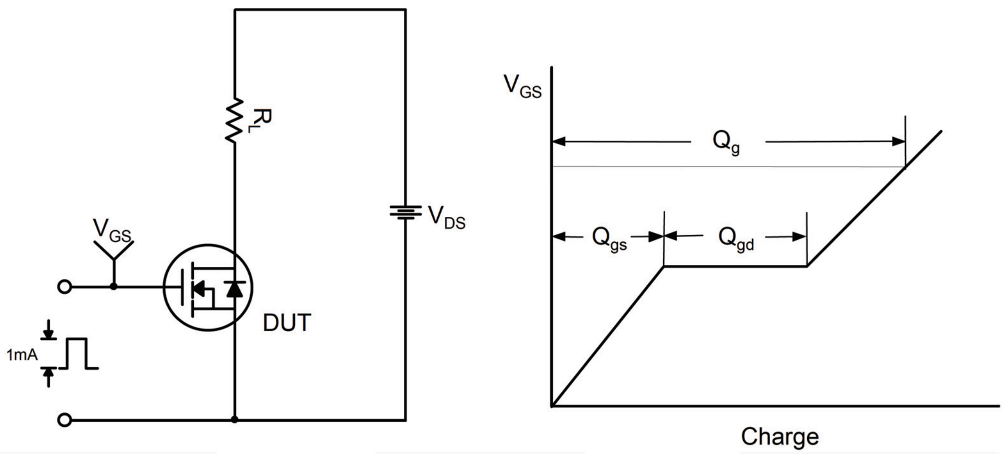


Figure 13. Resistive Switching Test Circuit & Waveforms

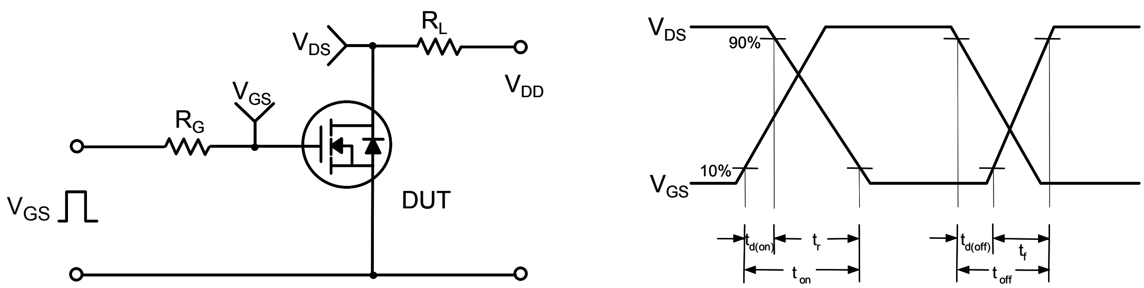


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

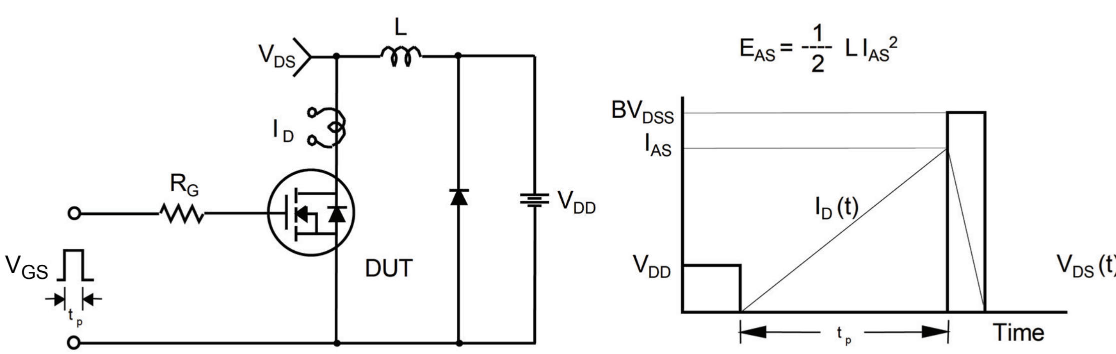
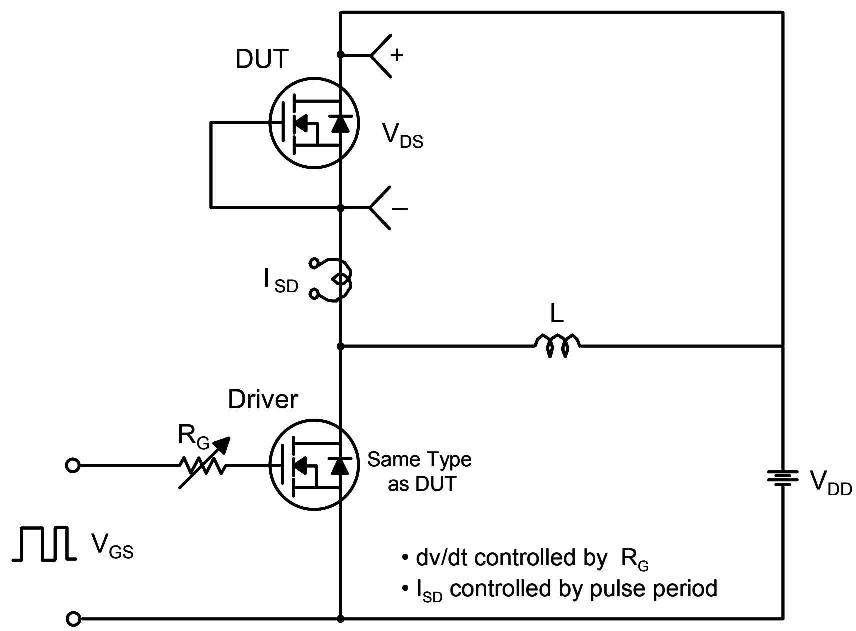
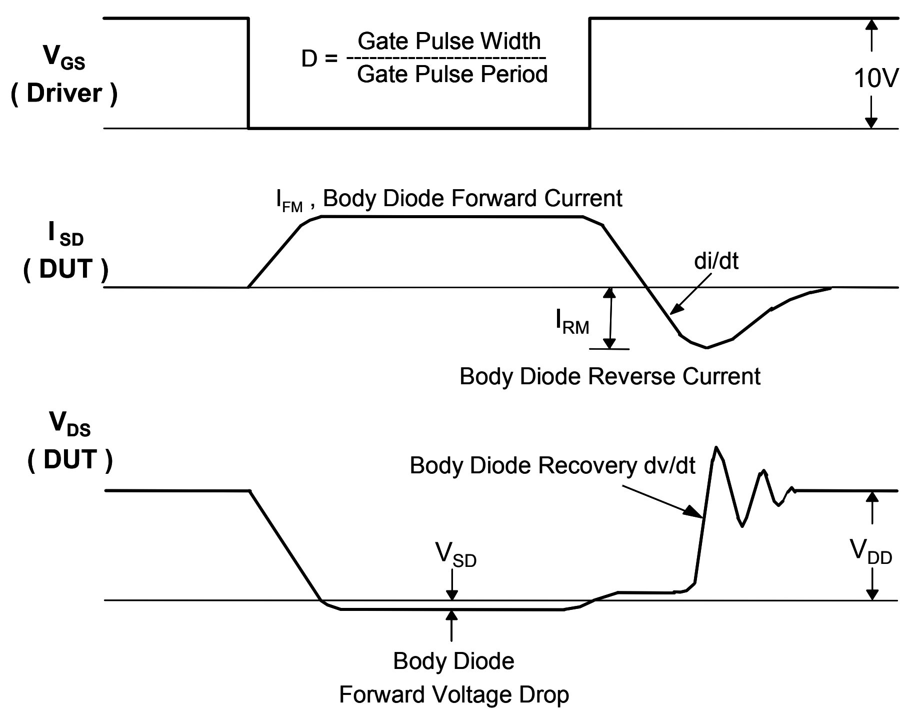


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

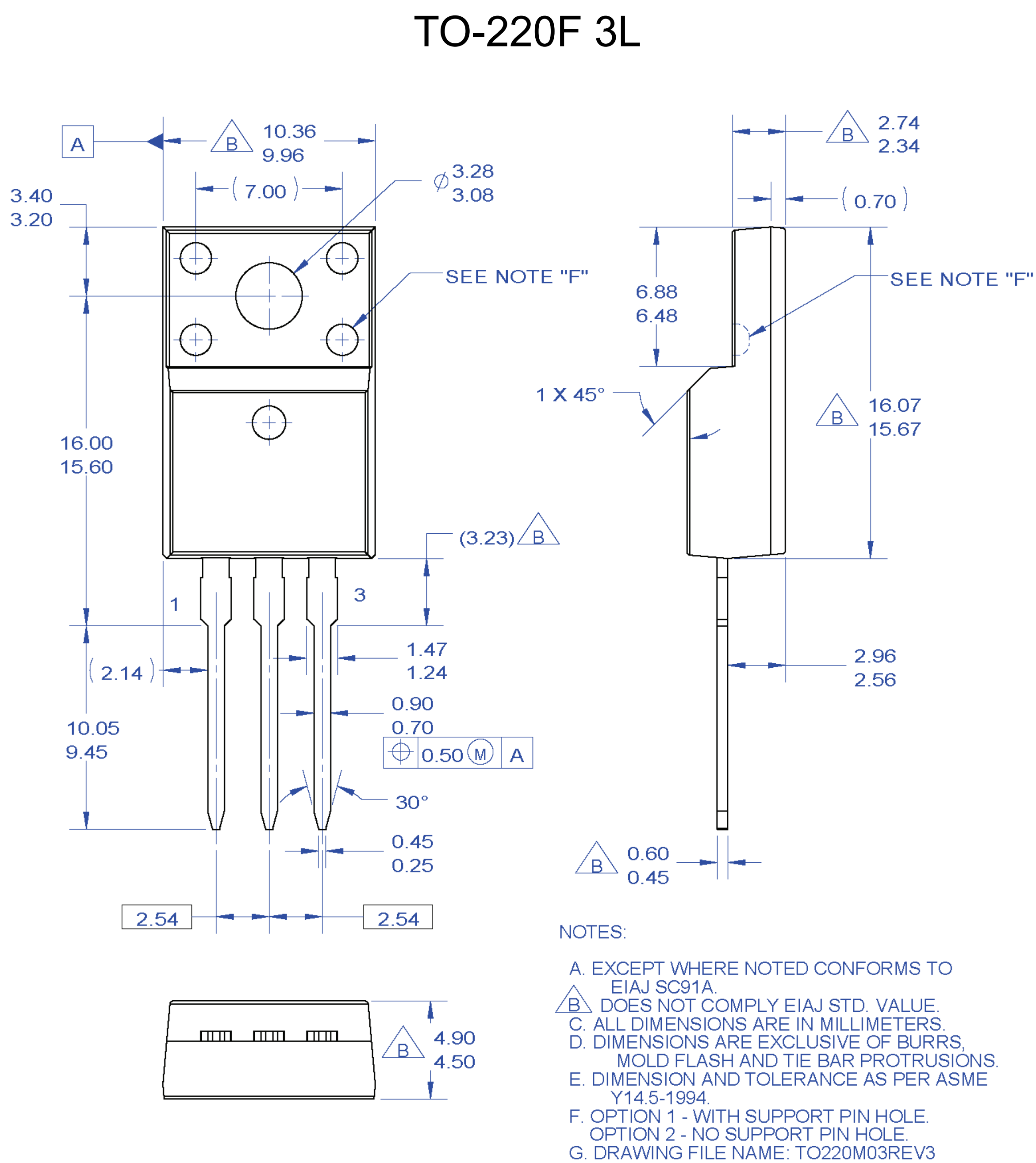


Figure 16. TO220, Molded, 3LD, Full Pack, EIAJ SC91, Straight Lead

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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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